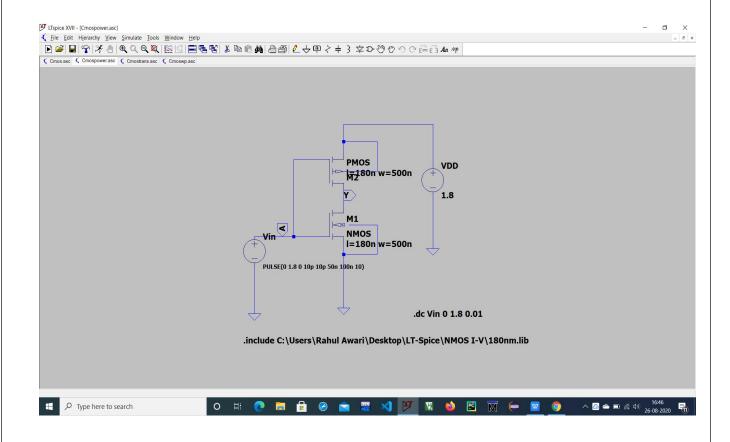
LAB ASSESSMENT -2 NAME: Rahul Mahesh Awari REGISTER NUMBER: 18BEC2014 SUBJECT: VLSI SYSTEM DESIGN (ECE3002-ELA) SLOT: L43 + L44 FACULTY: PROF. JAGANNADHA NAIDU K

CMOS INVERTER

AIM:

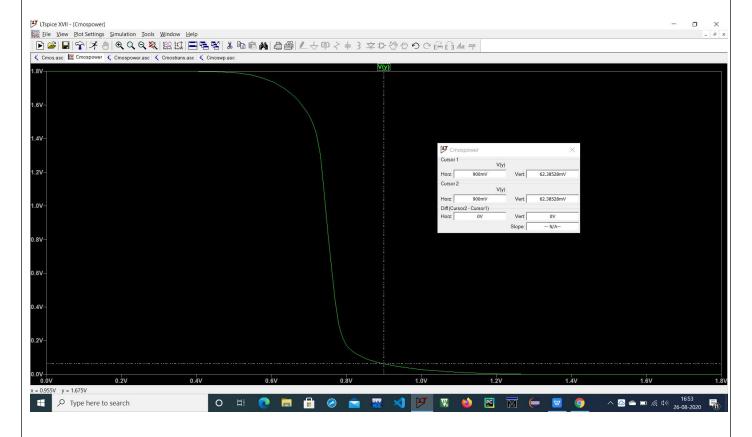
- 1) To Plot DC Analysis of CMOS Inverter.
- 2) To Plot DC Analysis with variable width of PMOS.
- 3) To plot the Transient analysis and to calculate the propagation delay.
- 4) To plot and Calculate Average Power.

SCHEMATIC:



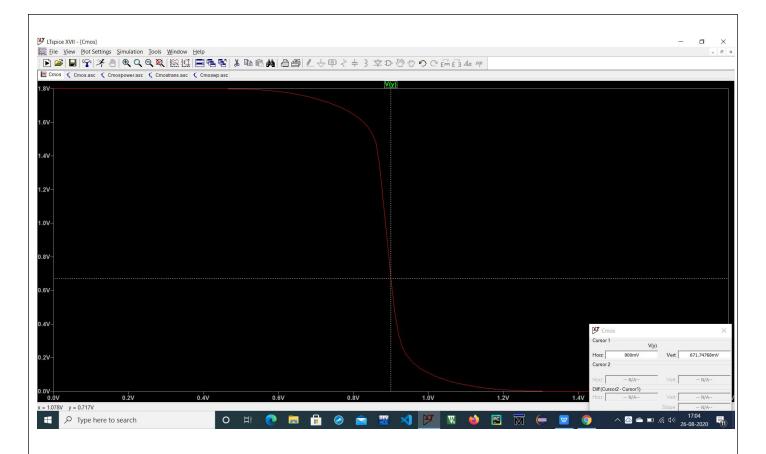
GRAPHS:-

- 1) To plot Transfer characteristics of CMOS Inverter.
 - a) PMOS:-length=180n,Width=500n
 - b) NMOS:- length=180n,Width=500n
 - c) Vin pulse
 - d) Vdd-1.8V

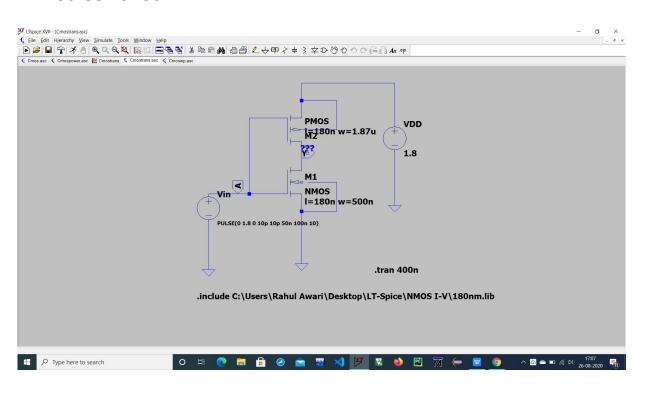


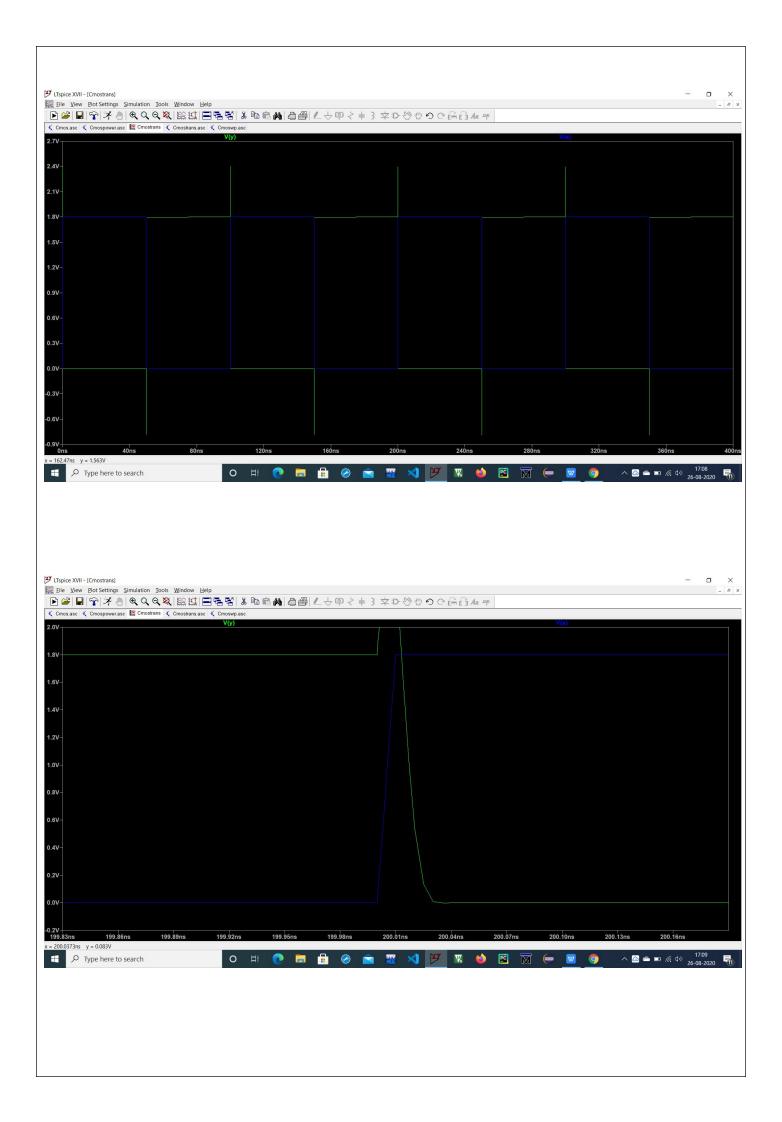
- 2) To Plot DC Analysis with variable width of PMOS.
 - a)PMOS:-length=180n,Width={wp}(1850n,1900n,10n)
 - b)NMOS:- length=180n,Width=500n
 - c)Vin-pulse
 - d)Vdd-1.8v

Screen Shot:-LTspice XVII - [Cmos.asc] 1 File Edit Hierarchy View Simulate Tools Window Help E Cmos € Cmos.asc € Cmospower.asc € Cmostrans.asc € Cmoswp.asc **PMOS** VDD 12180n w={wp} 1.8 .step param wp 1850n 1900n 10n M1 Vin l=180n w=500n PULSE(0 1.8 0 10p 10p 50n 100n 10) .dc Vin 0 1.8 0.01 $. include \ C: \ \ LT-Spice \ \ NMOS \ I-V \ \ 180nm. lib$ Type here to search _ 6 × Cmos (Cmos.asc (Cmosp .6V-0.8V-Type here to search



- 3) To plot the Transient analysis and to calculate the propagation delay.
 - a)PMOS:-length=180n,Width=1.87u
 - b)NMOS:- length=180n,Width=500n
 - c)Vin-pulse
 - d)Vdd-1.8v





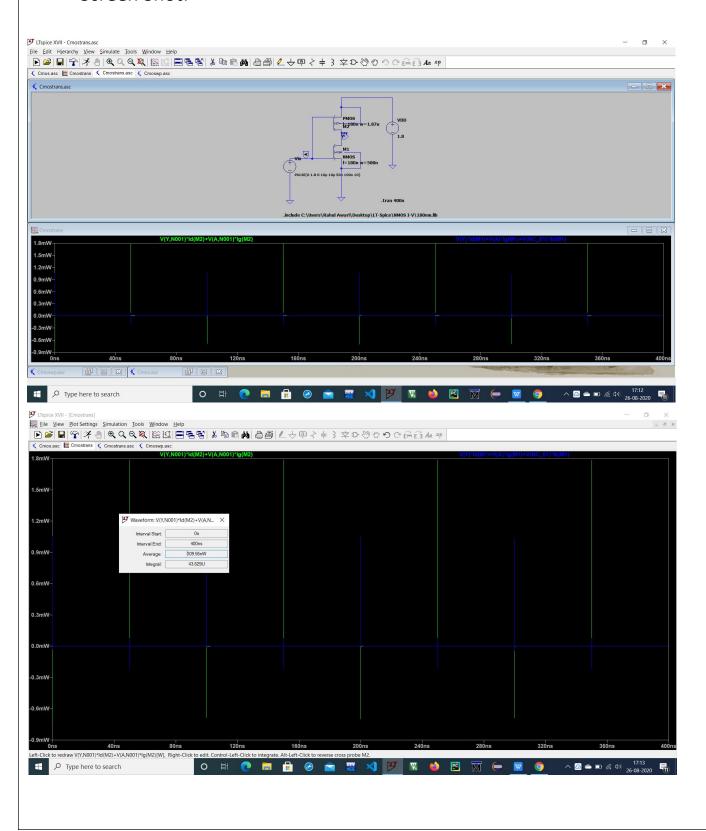
4) To plot and Calculate Average Power.

a)PMOS:-length=180n,Width=1.87u

b)NMOS:- length=180n,Width=500n

c)Vin-pulse

d)Vdd-1.8v



CALCULATIONS:

- 1) DC Analysis:-Horizontal - 62.93mV Vertical(Vin)-900mV
- Voltage at which Vout=Vin for variable wp. Wp=1.87u
- 3) Falling (tpdf) =10.95ps Rising (tpdr) = 13.03 ps Avg Delay = 12.15ps
- 4) Avg PMOS Power:- 109.554nW Avg NMOS Power:-88.57nW.

INFERENCE:

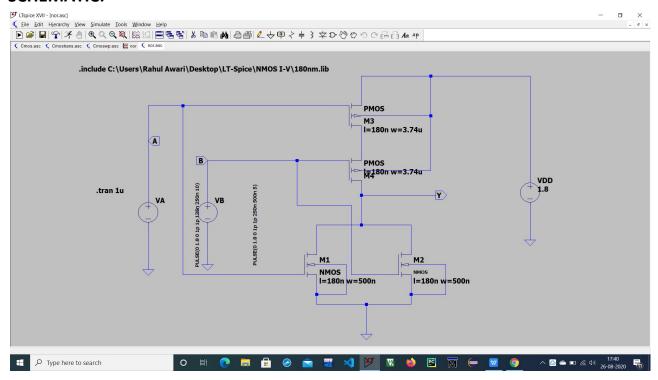
- 1) The CMOS inverter consists of a PMOS and an NMOS.
- 2) Pulse Voltage is used with following input:-
- a) V1=0
- b) V2=1.8
- c) Tdelay=0
- d) Trise=10p
- e) Tfall=10p
- f) Ton=50n
- g) Tperiod=100n
- h) Ncycles=10.
- 3) For variable width of wp, wp=1.87u is observed to be width of NMOS at which Horizontal voltage is same as Vertical Voltage.
- 4)Doing transient analysis, we calculated the propagation delay from the input and output signal at the rising edge and falling edge of both the signal. For delay propagation time is calculated at which horizontal voltage is Vdd/2 for both input and output for both rising and falling output.
- 5) Average power for both CMOS and NMOS is calculated along with graph.

NOR Implementation

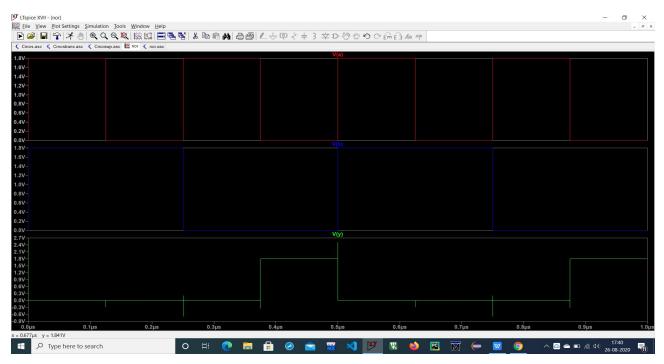
Aim:

- 1) To plot DC analysis of NOR logic implementation.
- 2) To observe output when propagated over both power source A,B.
- 3) Calculate Average Power.

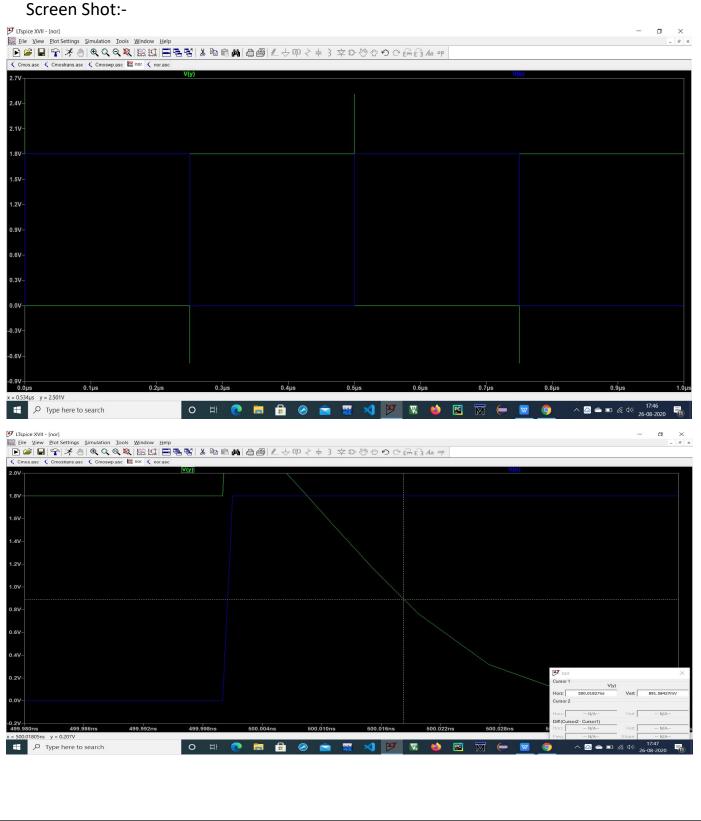
SCHEMATIC:-

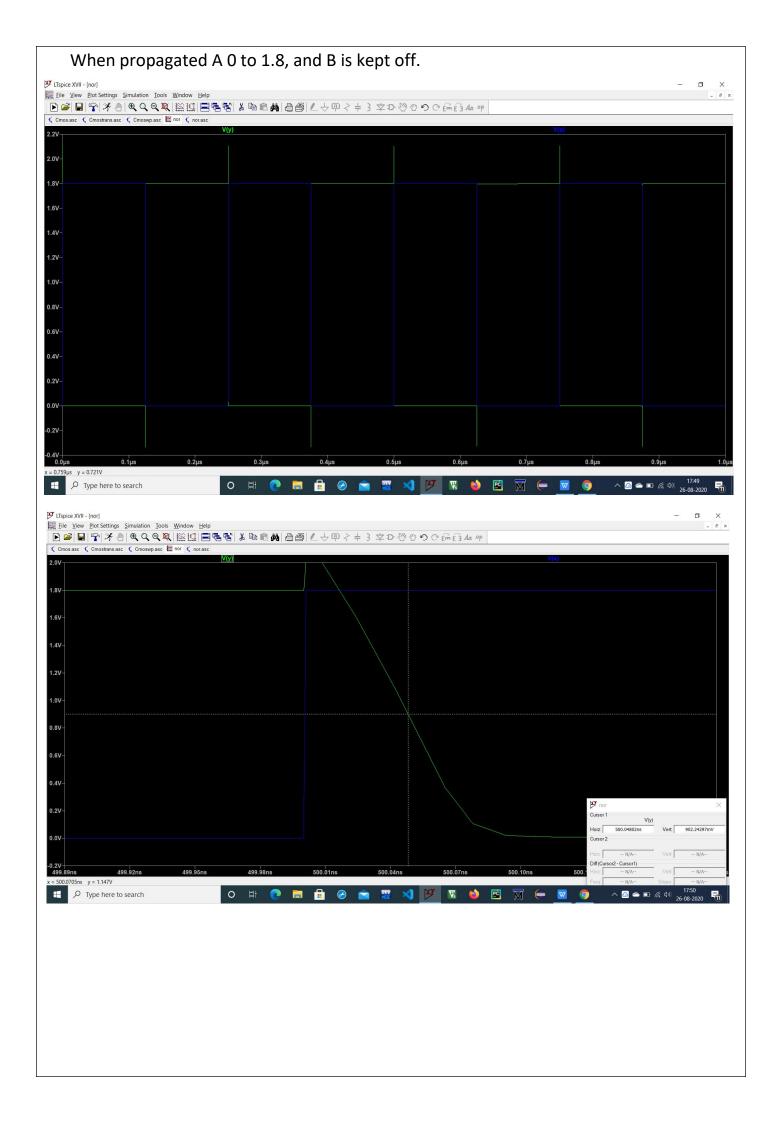


GRAPHS:-

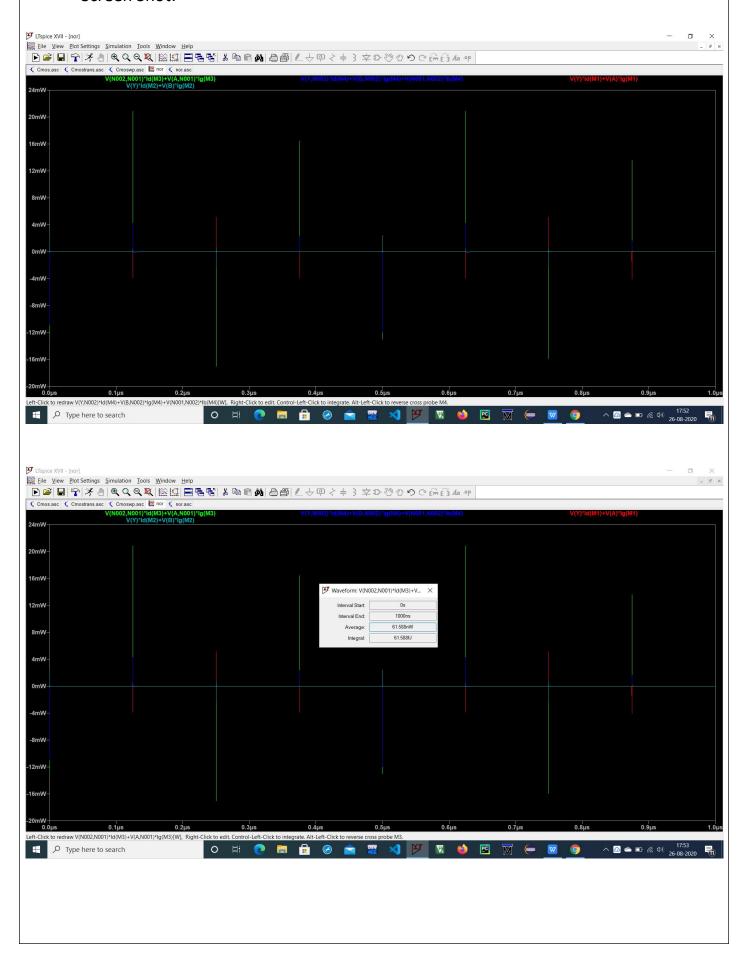


- A) PMOS:-length=180n,width-3.74u
- B) NMOS:-length=180n,width-500n
- C) Va, Vb-pulse
- D) Vdd-1.8v
- E) .tran 1u
- 2)To observe output when propagated over both power source A,B. When Propagated B 0 to 1.8 and A is kept off.





4) Avg Power



CALCULATIONS:-

1) For B(0 \rightarrow 1.8V)

A)Rise delay - 17.6ps

B)Fall delay - 16.5ps

C)Avg delay- 17.05ps

2) For A(0 \rightarrow 1.8V)

A)Rise delay - 46.3ps

B)Fall delay - 26.41ps

C) Avg delay - 36.35ps.

3)Total Average Power:-

1)	M1(NMOS)	15.62nW
2)	M2(NMOS)	13.78nW
3)	M4(PMOS)	43.099nW
4)	M3(PMOS)	61.539nW

Total Power: 139.107nW

Inference:-

1)

Inputs		Outputs
X	Υ	Z
0	0	1
0	1	0
1	0	0
1	1	0

- 2) Output Voltage plot is observed for both input voltage A and B.
- 3)When B is propagated from 0 to 1.8v ,time is noted at which vertical is Vdd/2 For both cases,firstly for falling output and rising input and vice versa. Same Is observed for A as well. The difference of time calculated for both input and Output curve is time delay and average is calculated.
- 4)The average power calculated is the cummulative power of all the four transistor.

5)When the input is steady at either a high or a low voltage (static condition) then one transistor is always off. Hence the current flowing is extremely small - equal to leakage current of the off transistor. As a result of this the static power dissipation extremely low.	the is